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[and dimensioned to penetrate into a recessed, metal bondpad on the die,] said raised portions dimensioned to penetrate into a pad on the die at the selected contact force with a penetration depth equal to a height of the raised portions but less than a thickness of the pad [to a penetration depth that is less than a thickness of the bondpad] while the surface of the contact limits further penetration of the contact into the pad at the selected contact force; and

a conductive trace formed on the substrate in electrical communication with the contact.

79. (twice amended) The attachment member as claimed in claim 78 [and] wherein the substrate and contact comprise silicon. [are formed of a material selected from the group consisting of silicon, germanium, silicon on sapphire, silicon on glass and a ceramic.]

80. (twice amended) The attachment member as claimed in claim 78 [and] wherein the raised portions comprise points. [are formed as pointed members.]

81. (twice amended) The attachment member as claimed in claim 78 [and] wherein the raised portions have a height of about 5000Å.

82. (twice amended) The attachment member as claimed in claim 78 [and] wherein the pad comprises a bondpad [is] recessed within a passivation layer formed on the die.

Sub. 1
I 2
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87. (amended) A member for making electrical connections for testing [discrete] unpackaged semiconductor dice, said member comprising:

a substrate for mounting within a test apparatus configured to retain a single unpackaged die and to bias the die against the substrate with a selected contact force;

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a contact formed on the substrate including a plurality of raised portions projecting from a surface of the contact, said raised portions shaped and dimensioned to penetrate into a [recessed metal] bondpad on the die at the selected contact force with a penetration depth equal to a height of the raised portions but less than a thickness of the bondpad [on the die to a penetration depth that is less than a thickness of the bondpad] while the surface of the contact limits further penetration of the contact into the bondpad at the selected contact force and

a conductive trace formed on the substrate in electrical communication with the contact.

88. (amended) The member as claimed in claim 87 [and] wherein the raised portions have a height of [about] at least 5000Å.

90. (amended) The member as claimed in claim 87 [and] wherein the substrate and contact comprise silicon. [are formed of a semiconductor material.]

91. (amended) The member as claimed in claim 87 [and] further comprising a second bond pad [formed on] in electrical communication with the conductive trace for wirebonding to the conductive trace.

92. (amended) A member for making temporary electrical connections for testing [discrete,] unpackaged semiconductor dice, said member comprising:

a substrate for mounting within a test apparatus configured to retain a single unpackaged die having a [recessed metal] bondpad and to bias the die and the substrate together with a selected contact force therebetween;

a contact formed on the substrate including a plurality of raised portions projecting from a surface of the contact,